

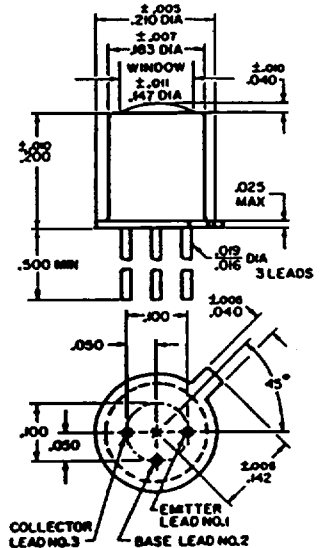


SLR-50L SERIES

NPN SILICON PLANAR EPITAXIAL PHOTODARLINGTON

General Description

The Silonex SLR-50L NPN silicon planar photodarlington series is mounted in a TO-18 high profile lensed hermetically sealed package. The high profile lensed cap allows an acceptance half angle of 10° measured from the optical axis to the half power point. The first stage base lead is connected for those applications where switching control and circuitry biasing is needed. This series of photodarlington devices is ideal in low light applications where higher gain is needed. Spectrally matched to Silonex infrared emitting diodes.



ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

- Collector-Emitter Voltage 40
- Collector-Base Voltage 60
- Emitter-Base Voltage 10
- Storage Temperature Range -65°C to $+150^\circ\text{C}$
- Operating Temperature Range -55°C to $+125^\circ\text{C}$
- Lead Soldering Temperature (5 Sec. 1/16" from case) 240°C
- Power Dissipation 250mW
- Derate linearly above 25°C $2\text{mW}/^\circ\text{C}$

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	SLR-50L1			SLR-50L2			SLR-50L3			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$I_L (I_{CEO})$	Collector Light Current	$V_{CE}=5V, H^*=0.2\text{mw}/\text{cm}^2$	0.5			2			4			mA
$I_D (I_{CEO})$	Collector Dark Current	$V_{CE}=5V, H=0$			100			100			100	nA
BV_{CEO}	Collector to Emitter Breakdown Voltage	$I_C=100\mu\text{A}$	40			40			40			Volts
BV_{CBO}	Collector to Base Breakdown Voltage	$I_C=100\mu\text{A}$	60			60			60			Volts
BV_{EBO}	Emitter to Base Breakdown Voltage	$I_E=100\mu\text{A}$	10			10			10			Volts
$V_{CE}(\text{SAT})$	Collector to Emitter Saturation Voltage	$I_C=10\text{mA}, I_B=0.05\text{mA}, H=0$			1.2			1.2			1.2	Volts
tr	Rise time	** $R_L=100\Omega, I_L=0.5\text{mA}$		100			100			100		μSec
tf	Fall time	$V_{CC}=5.0\text{ Volts}$		150			150			150		μSec

*The light source is a frosted Tungsten Incandescent lamp @ 2870°K
 **The light source is a gallium arsenide LED with a rise time less than 300ns

SIL05012